



Low-Voltage Single SPDT MICRO FOOT® Analog Switch

DESCRIPTION

The DG3000 is a single-pole/double-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 24 ns, t_{OFF} : 9 ns), low on-resistance ($r_{DS(on)}$: 1.4 Ω) and small physical size (MICRO FOOT, 6-bump), the DG3000 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG3000 is built on Vishay Siliconix's low voltage Jl2 process. An epitaxial layer prevents latchup. Break-before - make is guaranteed for DG3000.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the lead (Pb)-free device terminations. For MICRO FOOT analog switching products manufactured with tin/silver/copper (Sn/Ag/Cu) device terminations, the lead (Pb)-free "-E1" suffix is being used as a designator.

FEATURES

- MICRO FOOT[®] Chip Scale Package (1.07 x 1.57 mm)
- Low Voltage Operation (1.8 V to 5.5 V)
- Low On-Resistance r_{DS(on)}: 1.4 Ω
- Fast Switching t_{ON}: 24 ns, t_{OFF}: 9 ns
- Low Power Consumption
- TTL/CMOS Compatible

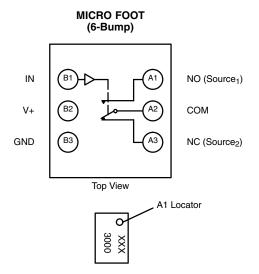
BENEFITS

- · Reduced Power Consumption
- · Simple Logic Interface
- High Accuracy
- Reduce Board Space

APPLICATIONS

- · Cellular Phones
- Communication Systems
- Portable Test Equipment
- · Battery Operated Systems
- PCM Cards
- PDA

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: 3000
xxx = Date/Lot Traceability Code

TRUTH TABLE						
Logic	NC	NO				
0	ON	OFF				
1	OFF	ON				

ORDERING INFORMATION						
Temp Range	Temp Range Package					
	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm Pitch 165 μm nom. bump height (Eutectic, SnPb)	DG3000DB-T1				
- 40 to 85 °C	MICRO FOOT: 6-Bump 3 x 2, 0.5 mm pitch, 238 μm nom. bump height (Lead (Pb)-free, Sn/Ag/Cu)	DG3000DB-T1-E1				

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^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Limit	Unit			
Referenced V+ to GND	- 0.3 to + 6 V	V				
IN, COM, NC, NO ^a		- 0.3 V to (V+ + 0.3 V)	7 v			
Continuous Current (Any Terminal)		± 50	mA			
Peak Current (Pulsed at 1 ms, 10 % du	± 200] ""				
Storage Temperature (D Suffix)	- 65 to 150	°C				
Package Reflow Conditions ^b						
VPR (Eutectic)		215				
IR/Convection (Eutectic)	220	°C				
IR/Convection (Lead (Pb)-free)	250					
Power Dissipation (Packages) ^c	6-Bump, 3 x 2 MICRO FOOT ^d	250	mW			

Notes:

- a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings. b. Refer to IPC/JEDEC (J-STD-020A). No hand/manual solder rework recommended. c. All bumps soldered to PC Board.

- d. Derate 3.1 mW/°C above 70 °C.

SPECIFICATIONS (V-	+ = 2.0 V)						
		Test Conditions Otherwise Unless Specified		Limits - 40 to 85 °C			
Parameter	Symbol	$V+ = 2.0 \text{ V}, \pm 10 \%, V_{IN} = 0.4 \text{ or } 1.6 \text{ V}^e$	Temp ^a	Min ^b	Typ ^c	Max ^b	Unit
Analog Switch			•				
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
On-Resistance	r _{ON}	V+ = 1.8 V, V _{COM} = 1.0 V, I _{NO} , I _{NC} = 10 mA	Room Full ^d		17	20 22.5	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 1.8 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		14		22
Cuitab Off Laglance Command	I _{NO(off)} I _{NC(off)}	V+ = 2.2 V	Room Full ^d	- 700 - 11		700 11	pA nA
Switch Off Leakage Current ^f	I _{COM(off)}	V_{NO} , $V_{NC} = 0.5 \text{ V/1.5 V}$, $V_{COM} = 1.5 \text{ V/0.5 V}$	Room Full ^d	- 700 - 11		700 11	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 2.2 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 0.5 \text{ V}/1.5 \text{ V}$	Room Full ^d	- 700 - 11		700 11	pA nA
Digital Control							
Input High Voltage	V_{INH}		Full	1.6			V
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitanced	C _{in}		Full		5		pF
Input Current ^d	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics					•		
Turn-On Time	t _{ON}	V 45VB 200 0 05 5	Room Full ^d		61	76 79	
Turn-Off Time	t _{OFF}	V_{NO} or V_{NC} = 1.5 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full ^d		17	33 36	ns
Break-Before-Make Time	t _d		Room	1	45		
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		2		рC
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$, $f = 1 MHz$	Room		- 61		dB
Crosstalk ^d	X _{TALK}	$II_L = 30.52, O_L = 3.61, I = 1.101 \square 2$	Room		- 67		uB
NO, NC Off Capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 or V+, f = 1 MHz			31		pF
Channel-On Capacitance ^d	C _{ON}	Room			98		
Power Supply							
Power Supply Range	V+			1.8		2.2	V
Power Supply Current ^d	l+	V 0 or V-			0.1	1.0	μΑ
Power Consumption	P _C	$V_{IN} = 0 \text{ or } V+$				2.2	μW







Parameter	Symbol	Test Conditions Otherwise Unless Specified	Temp ^a	Limits - 40 to 85 °C		Unit	
		$V+ = 3 V$, $\pm 10 \%$, $V_{IN} = 0.4 \text{ or } 2.0 V^e$		Min ^b	Typ ^c	Max ^b	J
Analog Switch							
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
On-Resistance ^d	r _{ON}	$V+ = 2.7 \text{ V}, V_{COM} = 1.5 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		3.3 3.4	4.1 4.2	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 2.7 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		1.3		52
Switch Off Leakage Current ^f	I _{NO(off)} I _{NC(off)}	V+ = 3.3 V	Room Full	- 800 - 13		800 13	pA nA
Switch Off Leakage Current	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V/3 V}$, $V_{COM} = 3 \text{ V/1 V}$	Room Full	- 800 - 13		800 13	pA nA
Channel-On Leakage Current ^f	I _{COM(on)}	$V+ = 3.3 \text{ V}, V_{NO}, V_{NC} = V_{COM} = 1 \text{ V/3 V}$	Room Full	- 800 - 13		800 13	pA nA
Digital Control							•
Input High Voltage	V _{INH}		Full	2			V
Input Low Voltage	V _{INL}		Full			0.4	v
Input Capacitance ^d	C _{in}		Full		5		pF
Input Current ^d	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics							•
Turn-On Time ^d	t _{ON}	V 22V 20V B 200 C 25 pF	Room Full		34	49 52	
Turn-Off Time ^d	t _{OFF}	V_{NO} or V_{NC} = 2.0 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full		12	30 33	ns
Break-Before-Make Time ^d	t _d		Room	1	23		
Charge Injection ^d	Q_{INJ}	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω , Figure 3	Room		4		рC
Off-Isolation ^d	OIRR	$R_1 = 50 \Omega, C_1 = 5 pF, f = 1 MHz$	Room		- 61		dB
Crosstalk ^d	X _{TALK}	11 - 30 34, 0[- 3 β1, 1 - 1 101112	Room		- 67		ub
NO, NC Off Capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 or V+, f = 1 MHz	Room		31		pF
Channel-On Capacitanced	C _{ON}	R			47		
Power Supply							
Power Supply Range	V+			2.7		3.3	V
Power Supply Current ^d	l+	V _{IN} = 0 or V+			0.1	1.0	μΑ
Power Consumption	P _C	- IIV = 0 01 1 1				3.3	μW



SPECIFICATIONS (V		Test Conditions		Limits			
Parameter	Symbol	Otherwise Unless Specified	Temp ^a		40 to 85 °		Unit
		$V+ = 5 V$, $\pm 10 \%$, $V_{IN} = 0.8 \text{ or } 2.4 V^e$		Min ^b	Typ ^c	Max ^b	
Analog Switch			1		1	ı	1
Analog Signal Range ^d	$V_{NO}, V_{NC} V_{COM}$		Full	0		V+	V
On- Resistance	r _{ON}	$V+ = 4.5 \text{ V}, V_{COM} = 3 \text{ V}, I_{NO}, I_{NC} = 10 \text{ mA}$	Room Full		1.4 1.6	2.3 2.8	Ω
r _{ON} Flatness ^d	r _{ON} Flatness	$V+ = 4.5 \text{ V}, V_{COM} = 0 \text{ to } V+, I_{NO}, I_{NC} = 10 \text{ mA}$	Room		0.5		52
Switch Off Leakage Current	I _{NO(off)} I _{NC(off)}	V+ = 5.5 V	Room Full	- 1.2 - 21		1.2 21	
owner on Leanage ourient	I _{COM(off)}	V_{NO} , $V_{NC} = 1 \text{ V}/4.5 \text{ V}$, $V_{COM} = 4.5 \text{ V}/1 \text{ V}$	Room Full	- 1.2 - 21		1.2 21	nA
Channel-On Leakage Current	I _{COM(on)}	V+ = 5.5 V, V+ = 5.5 V $V_{NO}, V_{NC} = V_{COM} = 1 V/4.5 V$	Room Full	- 1.2 - 21		1.2 21	
Digital Control							•
Input High Voltage	V_{INH}		Full	2.4			V
Input Low Voltage	V_{INL}		Full			0.8	V
Input Capacitance	C _{in}		Full		5		pF
Input Current	I _{INL} or I _{INH}	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics			•				•
Turn-On Time ^d	t _{ON}	V or V = 2 V B = 200 O C = 25 pE	Room Full		24	36 39	
Turn-Off Time ^d	t _{OFF}	V_{NO} or V_{NC} = 3 V, R_L = 300 Ω , C_L = 35 pF Figures 1 and 2	Room Full		9	22 25	ns
Break-Before-Make Time ^d	t _d		Room	1	15		
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V, } R_{GEN} = 0 \Omega, \text{ Figure 3}$	Room		38		рС
Off-Isolation ^d	OIRR	D - 50 0 C - 5 pE f - 1 MU-	Room		- 61		40
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 1 MHz$	Room		- 67		dB
Source-Off Capacitance ^d	$C_{NO(off)} \ C_{NC(off)}$	V _{IN} = 0 or V+, f = 1 MHz	Room		30		pF
Channel-On Capacitance ^d	C _{ON}		Room		96]
Power Supply			•			•	
Power Supply Range	V+			4.5		5.5	V
Power Supply Current	l+	V _{IN} = 0 or V+			0.1	1.0	μΑ
Power Consumption	P_{C}	VIN = O OI V+				5.5	μW

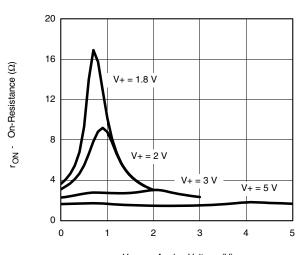
Notes:

- a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_{IN} = input voltage to perform proper function.
- f. Guaranteed by 5 V leakage testing, not production tested.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

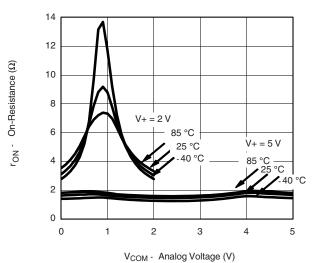


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

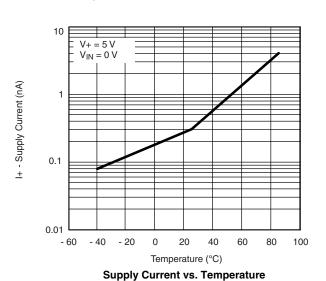


V_{COM} - Analog Voltage (V) $r_{\mbox{\scriptsize ON}}$ vs. $V_{\mbox{\scriptsize COM}}$ and Supply Voltage

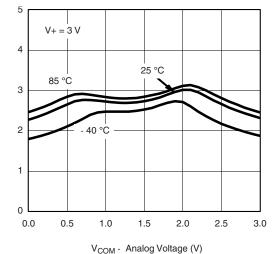
 r_{ON} - On-Resistance (Ω)



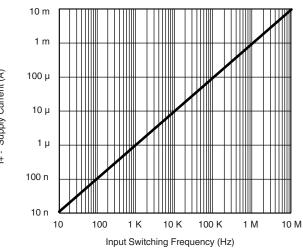
r_{ON} vs. Analog Voltage and Temperature



I+ - Supply Current (A) 10 μ 1 μ



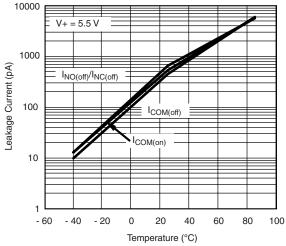
r_{ON} vs. Analog Voltage and Temperature



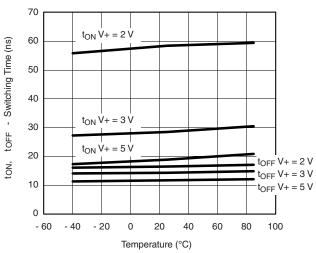
Supply Current vs. Input Switching Frequency

VISHAY

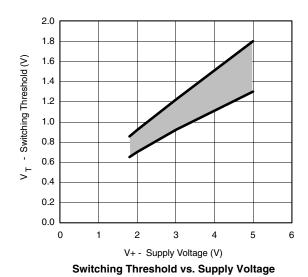
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Leakage Current vs. Temperature

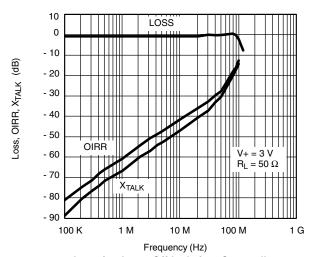


Switching Time vs. Temperature and Supply Voltage

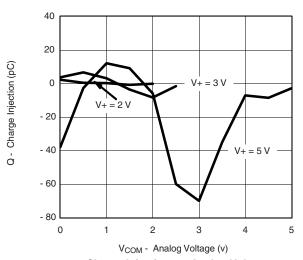


200 V + = 5 VT = 25 °C 0 - 200 Leakage Current (pA) - 400 $I_{NO(off)}/I_{NC(off)}$ I_{COM(on)} - 600 - 800 I_{COM(off)} - 1000 - 1200 2 3 5 $V_{COM},\,V_{NO},\,V_{NC}$ - Analog Voltage

Leakage vs. Analog Voltage



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Charge Injection vs. Analog Voltage



TEST CIRCUITS

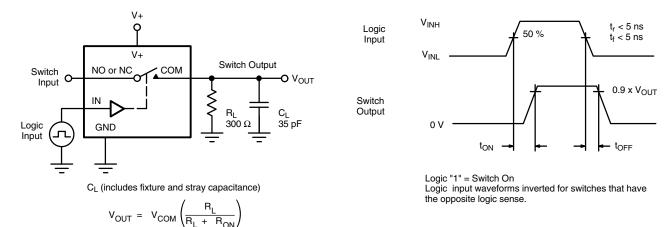


Figure 1. Switching Time

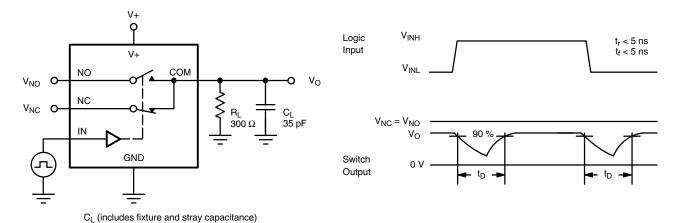


Figure 2. Break-Before-Make Interval

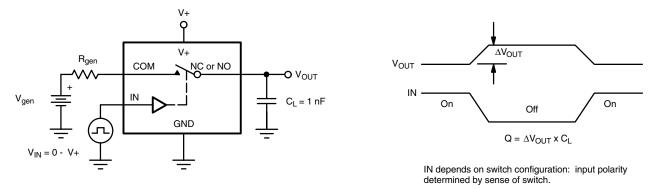


Figure 3. Charge Injection

VISHAY.

TEST CIRCUITS

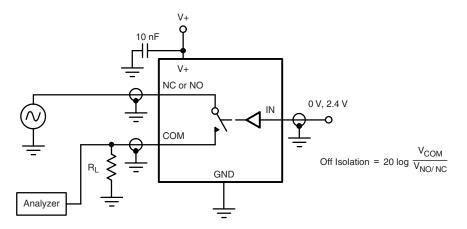


Figure 4. Off-Isolation

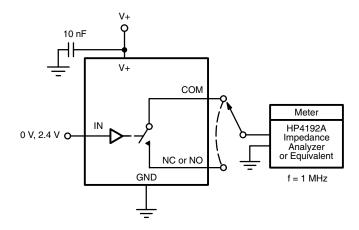
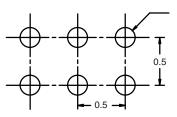


Figure 5. Channel Off/On Capacitance



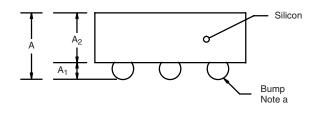
PACKAGE OUTLINE

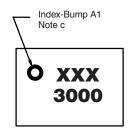
MICRO FOOT: 6-BUMP (3 x 2, 0.5 mm PITCH)



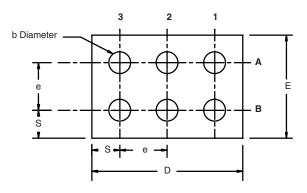
6 x Ø 0.150 ~ 0.229 Note b Solder Mask Ø ~ Pad Dia. + 0.1

Recommended Land Pattern





Top Side (Die Back)



Notes (Unless Otherwise Specified):

- a. Bump is Eutectic 63/57 Sn/Pb or Lead (Pb)-free Sn/Ag/Cu.
- b. Non-solder mask defined copper landing pad.
- c. Laser Mark on silicon die back; no coating. Shown is not actual marking; sample only.

EUTECTIC (Sn/Pb)						
	Millim	eters ^a	Inc	hes		
Dim	Min	Max	Min	Max		
Α	0.615	0.715	0.0242	0.0281		
A ₁	0.140	0.190	0.0055	0.0075		
A ₂	0.470	0.495	0.0185	0.0195		
b	0.180	0.250	0.0071	0.0098		
D	1.555	1.585	0.0612	0.0624		
E	1.055	1.085	0.0415	0.0427		
е	0.5 B	ASIC	0.0197	BASIC		
S	0.278	0.293	0.0109	0.0115		

LEAD (Pb)-FREE (Sn/Ag/Cu)							
	Millim	Millimeters ^a Inches					
Dim	Min	Max	Min	Max			
Α	0.688	0.753	0.0271	0.0296			
A ₁	0.218	0.258	0.0086	0.0102			
A ₂	0.470	0.495	0.0185	0.0195			
b	0.306	0.346	0.0120	0.0136			
D	1.555	1.585	0.0612	0.0624			
E	1.055	1.085	0.0415	0.0427			
е	0.5 B	ASIC	0.0197 BASIC				
S	0.278	0.293	0.0109 0.011				

Notes:

a. Use millimeters as the primary measurement.

Notes:

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Vishay

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